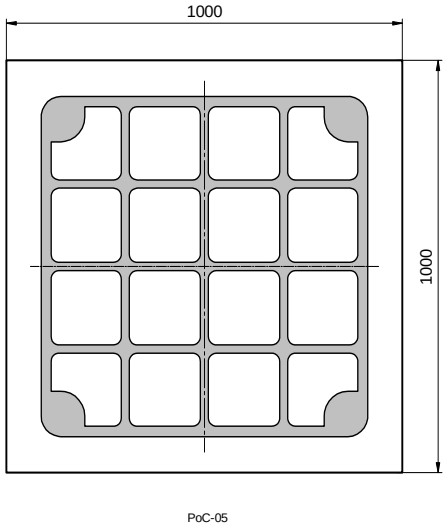
LED - Chip ELC-950-11

01.12.2011 rev. 03

Radiation	Type	Technology	Electrodes
Infrared	DH	AlGaAs/GaAs	P (anode) up



typ. dimensions (µm)

typ. thickness
260 (±20) µm

anode
gold alloy, 1.5 µm

cathode
gold alloy, 0.5 µm,

Optical and Electrical Characteristics

T_{amb} = 25℃, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F		1.1	1.3	V
Forward voltage[1]	I_F = 350 mA	V_F		1.3	1.7	V
Reverse voltage	I_R = 100 µA	V_R	5			V
Radiant power[1]	I_F = 20 mA	Φ_e	1.0	1.6		mW
Radiant power[1]	I_F = 350 mA	Φ_e	20	30		mW
Peak wavelength	I_F = 20 mA	λ_P	935	950	960	nm
Spectral bandwidth at 50%	I_F = 20 mA	$\Delta\lambda_{0.5}$		50		nm
Switching time	I_F = 20 mA	t_r, t_f		900/700		ns

[1] Measured on bare chip glued on a Ø 8 x 1mm Cu header with JENOPTIK Polymer Systems equipment (for information only)

Labeling

Type	Lot N°	Φ_e(typ) [mW]	V_F(typ) [V]	Quantity
ELC-950-11				

Packing: Chips on adhesive film with wire-bond side on top

JENOPTIK Polymer Systems GmbH, D-12555 Berlin, Köpenicker Str.325 b, Haus 201
Tel.: +49-30-6576 2543, Fax : +49-30-6576 2545